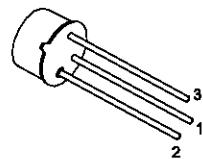


LOW NOISE GENERAL PURPOSE AUDIO AMPLIFIERS

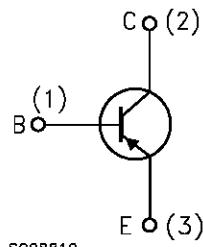
DESCRIPTION

The BC177 is a silicon planar epitaxial PNP transistors in TO-18 metal case. It is suitable for use in driver stages, low noise input stages and signal processing circuits of television receivers. The NPN complement is BC107.



TO-18

INTERNAL SCHEMATIC DIAGRAM



SC08810

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	-50	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-45	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-100	mA
I_{CM}	Collector Peak Current	-200	mA
P_{tot}	Total Dissipation at $T_{amb} \leq 25^\circ\text{C}$	0.3	W
T_{stg}	Storage Temperature	-65 to 175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

THERMAL DATA

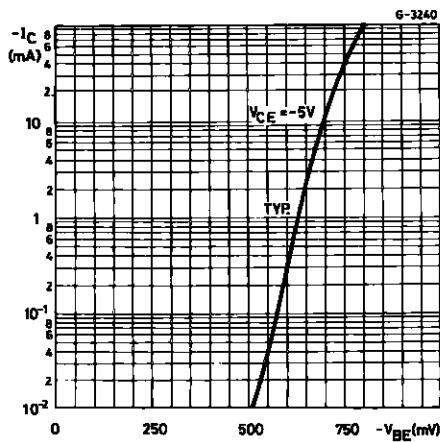
$R_{\text{thj-case}}$	Thermal Resistance Junction-Case	Max	200	$^{\circ}\text{C/W}$
$R_{\text{thj-amb}}$	Thermal Resistance Junction-Ambient	Max	500	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

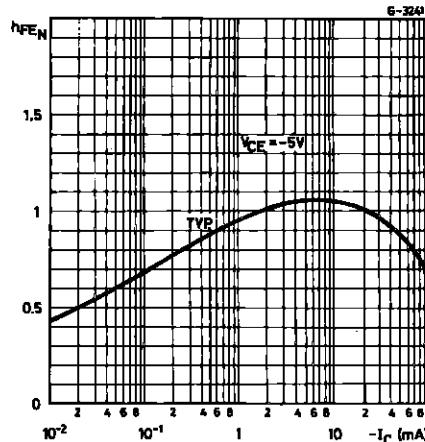
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{\text{BE}} = 0$)	$V_{\text{CE}} = -20 \text{ V}$ $V_{\text{CE}} = -20 \text{ V} \quad T_{\text{amb}} = 150^{\circ}\text{C}$		-1	-100 -10	nA μA
$V_{(\text{BR})\text{CES}}$	Collector-Emitter Breakdown Voltage ($V_{\text{BE}} = 0$)	$I_{\text{C}} = -10 \mu\text{A}$	-50			V
$V_{(\text{BR})\text{CEO}}^*$	Collector-Emitter Breakdown Voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = -2 \text{ mA}$	-45			V
$V_{(\text{BR})\text{EBO}}$	Emitter-Base Breakdown Voltage ($I_{\text{C}} = 0$)	$I_{\text{E}} = -10 \mu\text{A}$	-5			V
$V_{\text{CE}(\text{sat})}^*$	Collector-Emitter Saturation Voltage	$I_{\text{C}} = -10 \text{ mA} \quad I_{\text{B}} = -0.5 \text{ mA}$ $I_{\text{C}} = -100 \text{ mA} \quad I_{\text{B}} = -5 \text{ mA}$		-75 -200	-250	mV mV
$V_{\text{BE}(\text{sat})}^*$	Base-Emitter Saturation Voltage	$I_{\text{C}} = -10 \text{ mA} \quad I_{\text{B}} = -0.5 \text{ mA}$ $I_{\text{C}} = -100 \text{ mA} \quad I_{\text{B}} = -5 \text{ mA}$		-720 -860		mV mV
$V_{\text{BE}(\text{on})}^*$	Base-Emitter On Voltage	$I_{\text{C}} = -2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V}$	-550	-640	-750	mV
h_{fe}^*	Small Signal Current Gain	$I_{\text{C}} = -2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V} \quad f = 1\text{KHz}$ Gr. A Gr. B		125 240	260 500	
f_T	Transition Frequency	$I_{\text{C}} = -10 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V} \quad f = 100 \text{ MHz}$		200		MHz
C_{CBO}	Collector Base Capacitance	$I_{\text{E}} = 0 \quad V_{\text{CB}} = -10 \text{ V}$		5		pF
NF	Noise Figure	$I_{\text{C}} = -0.2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V}$ $f = 1\text{KHz} \quad R_g = 2\text{K}\Omega \quad B = 200\text{Hz}$		2	10	dB
h_{ie}	Input Impedance	$I_{\text{C}} = -2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V} \quad f = 1\text{KHz}$ Gr. A Gr. B		2.7 5.2		K Ω K Ω
h_{re}	Reverse Voltage Ratio	$I_{\text{C}} = -2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V} \quad f = 1\text{KHz}$ Gr. A Gr. B		2.7 4.5		10^{-4} 10^{-4}
h_{oe}	Output Admittance	$I_{\text{C}} = -2 \text{ mA} \quad V_{\text{CE}} = -5 \text{ V} \quad f = 1\text{KHz}$ Gr. A Gr. B		25 35		μS μS

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

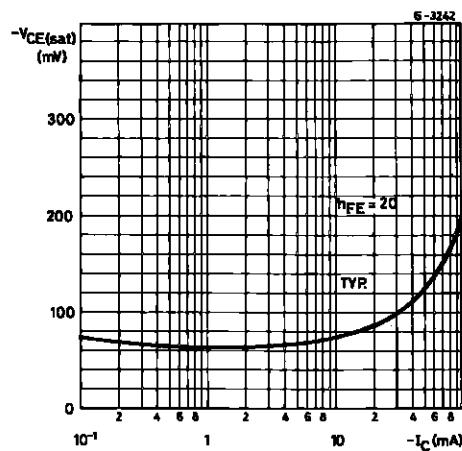
DC Transconductance.



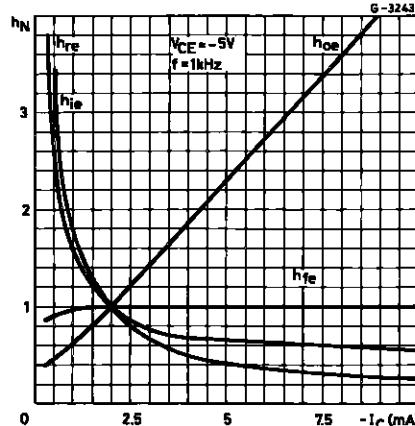
DC Normalized Current Gain.



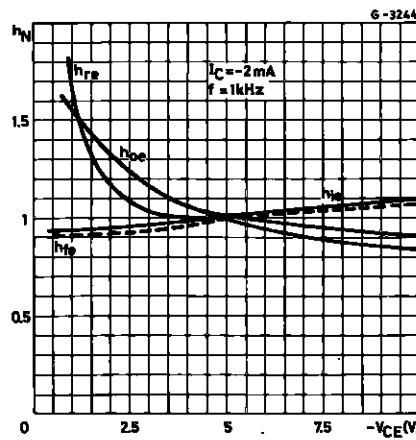
Collector-emitter Saturation Voltage.



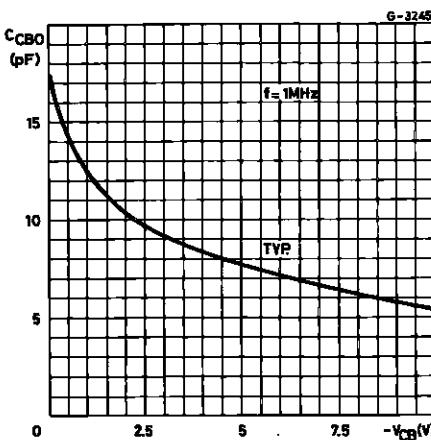
Normalized h Parameters.



Normalized h Parameters.

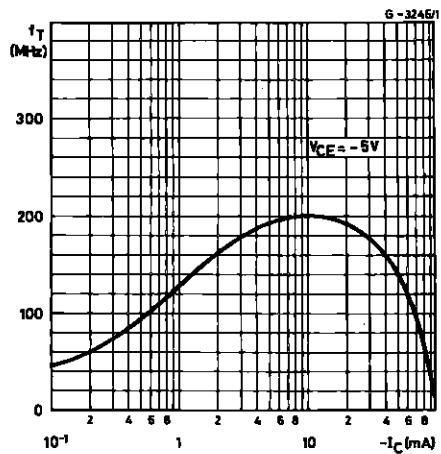


Collector-base Capacitance.

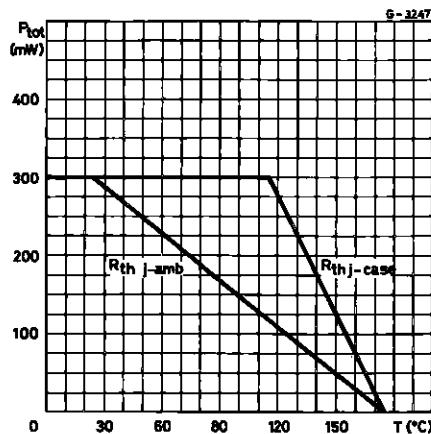


BC177

Transition Frequency.

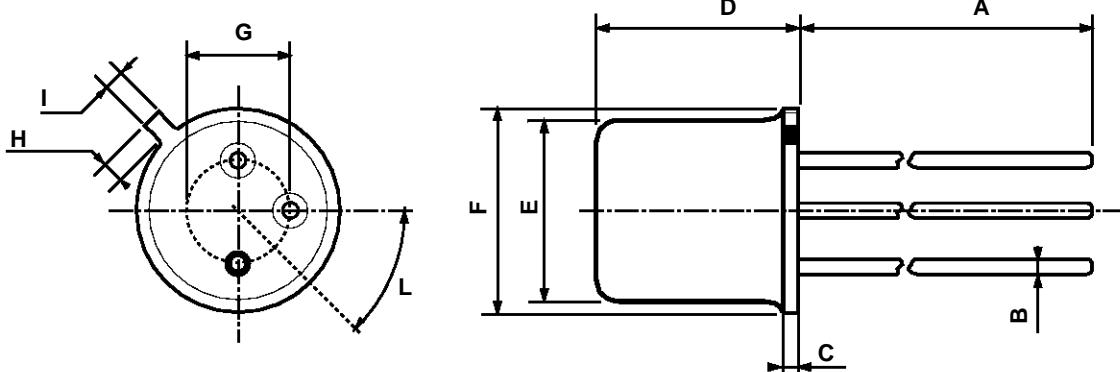


Power Rating Chart.



TO-18 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		12.7			0.500	
B			0.49			0.019
D			5.3			0.208
E			4.9			0.193
F			5.8			0.228
G	2.54			0.100		
H			1.2			0.047
I			1.16			0.045
L	45°			45°		



0016043

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